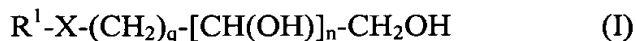


AMENDMENTS TO THE CLAIMS

Claim 1 (Original): A polishing liquid composition for polishing a surface to be polished comprising an insulating layer and a metal layer, the polishing liquid composition comprising a compound having a structure in which each of two or more adjacent carbon atoms has a hydroxyl group in a molecule, and water, wherein the compound having a structure in which each of two or more adjacent carbon atoms has a hydroxyl group in a molecule is represented by the formula (I):



wherein

R^1 is a hydrocarbon group having 1 to 24 carbon atoms;

X is a group represented by

$(CH_2)_m$, wherein m is 1,

oxygen atom,

sulfur atom,

COO group,

OCO group,

a group represented by NR^2 or

$O(R^2O)P(O)O$, wherein R^2 is hydrogen atom or a hydrocarbon group having 1 to 24 carbon atoms;

q is 0 or 1; and

n is an integer of 1 to 4.

Claim 2 (Original): The polishing liquid composition according to claim 1, further comprising an organic acid.

Claim 3 (Original): The polishing liquid composition according to claim 2, wherein the organic acid is an etching agent.

Claim 4 (Original): The polishing liquid composition according to claim 1, further comprising an etching agent comprising an inorganic acid.

Claim 5 (Currently Amended): A polishing liquid composition for polishing a surface to be polished comprising an insulating layer and a metal layer, the polishing liquid composition comprising an aliphatic carboxylic acid having 7 to 24 carbon atoms and/or a salt thereof, an etching agent comprising an organic acid, and water, wherein the organic acid of the etching agent is at least one selected from the group consisting of

A: aliphatic organic acids having 6 or less carbon atoms and one to three carboxyl groups;

B: aromatic organic acids having 7 to 10 carbon atoms and one to four carboxyl groups;

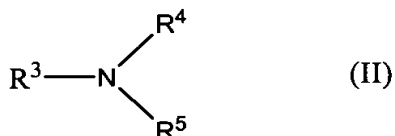
C: organic acids having 6 or less carbon atoms and one to four phosphonic groups; and

D: polyaminocarboxylic acids having in a molecule two or more structures represented by the formula (III):



Claim 6 (Currently Amended): A polishing liquid composition for polishing a surface to be polished comprising an insulating layer and a metal layer, the polishing liquid composition comprising

an amine compound represented by the following general formula (II):



wherein

R³ is a linear or branched alkyl group having 4 to 18 carbon atoms,
a linear or branched alkenyl group having 4 to 18 carbon atoms,
an aryl group having 6 to 18 carbon atoms, and
an aralkyl group having 7 to 18 carbon atoms;

each of R⁴ and R⁵, which may be identical or different, is

~~hydrogen atom,~~

a linear alkyl group having 1 to 8 carbon atoms or

a branched alkyl group having 3 to 8 carbon atoms, or

a group represented by H-(OR⁶)_z-, wherein R⁶ is a linear alkylene group having 1 to 3 carbon atoms, or

a branched alkylene group having 3 carbon atoms; and

Z is a number of 1 to 20, and/or a salt thereof,

an etching agent,

an oxidizing agent, and

water.

Claim 7 (Previously Presented): The polishing liquid composition according to Claim 1, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 8 (Canceled).

Claim 9 (Withdrawn – Currently Amended): ~~A process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method~~ comprising polishing a surface ~~to be polished comprising an insulating layer and a metal layer~~ using the polishing liquid composition of Claim 1, ~~thereby smoothening the semiconductor substrate.~~

Claim 10 (Canceled)

Claim 11 (Previously Presented): The polishing liquid composition according to claim 2, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 12 (Previously Presented): The polishing liquid composition according to claim 5, further comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 13 (Currently Amended): The polishing liquid composition according to claim 6, further ~~to~~ comprising an oxidizing agent, an abrasive or a mixture thereof.

Claim 14 (Withdrawn – Currently Amended): ~~A process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 2, thereby smoothening the semiconductor substrate.~~

Claim 15 (Withdrawn – Currently Amended): ~~A process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 5, thereby smoothening the semiconductor substrate.~~

Claim 16 (Withdrawn – Currently Amended): ~~A process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 6, thereby smoothening the semiconductor substrate.~~

Claim 17 (Withdrawn – Currently Amended): ~~A process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method comprising polishing a surface to be polished comprising an insulating layer and a metal layer using the polishing liquid composition of claim 7, thereby smoothening the semiconductor substrate.~~

Claim 18 (Withdrawn – Currently Amended): A ~~process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method~~ comprising polishing a surface ~~to be polished comprising an insulating layer and a metal layer~~ using the polishing liquid composition of claim 11, ~~thereby smoothening the semiconductor substrate.~~

Claim 19 (Withdrawn – Currently Amended): A ~~process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method~~ comprising polishing a surface ~~to be polished comprising an insulating layer and a metal layer~~ using the polishing liquid composition of claim 12, ~~thereby smoothening the semiconductor substrate.~~

Claim 20 (Withdrawn – Currently Amended): A ~~process for polishing a semiconductor substrate, method of using a polishing liquid composition, the method~~ comprising polishing a surface ~~to be polished comprising an insulating layer and a metal layer~~ using the polishing liquid composition of claim 13, ~~thereby smoothening the semiconductor substrate.~~

Claims 21-27 (Canceled)

Claim 28 (New) A method of making a polishing liquid composition, the method comprising

mixing water and a compound having a molecular structure in which each of two or more adjacent carbon atoms has a hydroxyl group; and

producing the polishing liquid composition of claim 1.

Claim 29 (New) A method of making a polishing liquid composition, the method comprising

mixing an aliphatic carboxylic acid having 7 to 24 carbon atoms and/or a salt thereof, an etching agent, an oxidizing agent and water; and
producing the polishing liquid composition of claim 5.

Claim 30 (New) A method of making a polishing liquid composition, the method comprising

mixing an amine compound, an etching agent, an oxidizing agent and water; and
producing the polishing liquid composition of claim 6.